Power LDMOS transistor

Rev. 1 — 19 April 2018

# 1. Product profile

## 1.1 General description

400 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 1805 MHz to 1880 MHz.

### Table 1.Typical performance

Typical RF performance at  $T_{case} = 25 \, ^{\circ}$ C in an asymmetrical Doherty demo circuit ( $V_{DS} = 32 \, V$ ) and production circuit ( $V_{DS} = 28 \, V$ );  $I_{Dq} = 860 \, mA$  (main);  $V_{GS(amp)peak} = 0.7 \, V$ , unless otherwise specified.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	ησ	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	1805 to 1880	28	56	16.5	49.0	–29.7 <mark>[1]</mark>
	1805 to 1880	32	93	17.0	49.5	–29.5 <mark>[1]</mark>

[1] Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability on CCDF.

## 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

## **1.3 Applications**

 RF power amplifiers for base stations and multi carrier applications in the 1805 MHz to 1880 MHz frequency range

# 2. Pinning information

Table 2. F	Pinning			
Pin	Description		Simplified outline	Graphic symbol
1	drain2 (peak)			0.7
2	drain1 (main)			2, 7
3	gate1 (main)		5	
4	gate2 (peak)			3
5	source	[1]		
6	video decoupling (peak)			۲ <u>ـ</u>
7	video decoupling (main)			1, 6 aaa-014884

[1] Connected to flange.

# 3. Ordering information

#### Table 3.Ordering information

Type number	Package				
	Name	Description	Version		
BLC10G18XS-400AVT	-	air cavity plastic earless flanged package; 6 leads	SOT1258-4		

# 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage		-	65	V
V <sub>GS(amp)main</sub>	main amplifier gate-source voltage		-6	+9	V
V <sub>GS(amp)peak</sub>	peak amplifier gate-source voltage		-6	+9	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1	1 -	225	°C
T <sub>case</sub>	case temperature	operating [1	<u>l</u> –40	+125	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

# 5. Thermal characteristics

#### Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$V_{DS} = 32 \text{ V}; \text{ I}_{Dq} = 800 \text{ mA (main)};$ $V_{GS(amp)peak} = 0,4 \text{ V}; \text{ T}_{case} = 80 ^{\circ}\text{C}$		
		P <sub>L</sub> = 56 W	0.32	k/W
		P <sub>L</sub> = 74 W	0.3	k/W

# 6. Characteristics

Table 6.	DC characteristics	

 $T_j = 25 \ ^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 1.44 mA	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 144 mA	1.5	2.0	2.5	V
V <sub>GSq</sub>	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 800 mA	-	2.2	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	2.8	μA
I <sub>DSX</sub>	drain cut-off current	V <sub>GS</sub> = V <sub>GS(th)</sub> + 3.75 V	-	26.5	-	А
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 9 V; V <sub>DS</sub> = 0 V	-	-	280	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 7.2 A	-	15.0	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ I <sub>D</sub> = 5.04 A	-	93	128	mΩ
Peak dev	vice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 2.98 mA	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 298 mA	1.5	2.0	2.5	V
V <sub>GSq</sub>	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 1600 mA	-	2.2	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	2.8	μA
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V$	-	47	-	А
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 9 V; V <sub>DS</sub> = 0 V	-	-	280	nA
<b>g</b> <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 14.9 A	-	28.5	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 10.43 A$	-	50	74	mΩ

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH;  $f_1$  = 1807.5 MHz;  $f_2$  = 1877.5 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 800 mA (main);  $V_{GS(amp)peak}$  = 0.7 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1805 MHz to 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L(AV)</sub> = 56 W	14.7	15.7	-	dB
RL <sub>in</sub>	input return loss	P <sub>L(AV)</sub> = 56 W	-	–15	–10	dB
$\eta_D$	drain efficiency	P <sub>L(AV)</sub> = 56 W	45	49	-	%
ACPR	adjacent channel power ratio	P <sub>L(AV)</sub> = 56 W	-	-28	-23	dBc

#### Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f = 1877.5 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 800 mA (main);  $V_{GS(amp)peak}$  = 0.7 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at a frequency of 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
PARO	output peak-to-average ratio	P <sub>L(AV)</sub> = 120 W	6.5	7.1	-	dB
P <sub>L(M)</sub>	peak output power	P <sub>L(AV)</sub> = 120 W	395	460	-	W

# 7. Test information

## 7.1 Ruggedness in Doherty operation

The BLC10G18XS-400AVT is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 32 V;  $I_{Dq}$  = 800 mA;  $V_{GS(amp)peak}$  = 0.62 V; f = 1807.5 MHz; P<sub>L</sub> = 185 W (5 dB OBO); 1-carrier W-CDMA, 100 % clipping.

## 7.2 Impedance information

#### Table 9. Typical impedance of main device

Measured load-pull data of main device;  $I_{Dq}$  = 800 mA (main);  $V_{DS}$  = 28 V; pulsed CW ( $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %).

f	Z <sub>S</sub> [1]	Z <sub>L</sub> <sup>[1]</sup>	P <sub>L</sub> [2]	η <mark>ρ [2]</mark>	G <sub>p</sub> [2]				
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)				
Maximun	Maximum power load								
1800	1.1 – j5.0	1.2 – j2.9	200	61.0	17.0				
1845	1.2 – j5.4	1.3 – j2.8	200	62.0	17.5				
1880	1.5 – j5.8	1.1 – j2.8	200	58.5	17.0				
Maximun	n drain efficiency	load							
1800	1.1 – j5.0	2.2 – j1.9	145	70.0	19.2				
1845	1.2 – j5.4	2.0 – j1.9	145	69.0	19.5				
1880	1.5 – j5.8	1.9 – j1.7	140	68.5	19.5				

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.

[2] At 3 dB gain compression.

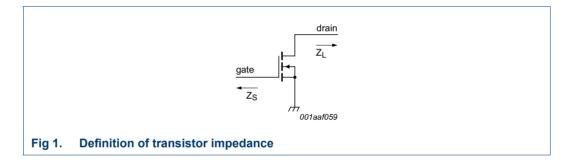
#### Table 10. Typical impedance of peak device

Measured load-pull data of peak device;  $I_{Dq} = 1600 \text{ mA}$  (peak);  $V_{DS} = 28 \text{ V}$ ; pulsed CW ( $t_p = 100 \mu \text{s}$ ;  $\delta = 10 \%$ ).

Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <mark>ρ <sup>[2]</sup></mark>	G <sub>p</sub> [2]
(Ω)	(Ω)	(W)	(%)	(dB)
n power load				
1.9 – j6.1	1.6 – j3.0	375	60.0	17.0
2.7 – j6.9	1.7 – j3.4	370	61.0	17.5
3.8 – j7.5	1.7 – j2.9	370	59.0	17.5
n drain efficiency	load			
1.9 – j6.1	2.8 – j2.3	295	67.5	19.0
2.7 – j6.9	2.2 – j1.9	280	67.0	19.3
3.8 – j7.5	2.0 – j1.9	280	67.0	19.4
	(Ω) <b>n power load</b> 1.9 – j6.1 2.7 – j6.9 3.8 – j7.5 <b>n drain efficiency</b> 1.9 – j6.1 2.7 – j6.9	( $\Omega$ )( $\Omega$ ) <b>n power load</b> $1.9 - j6.1$ $1.6 - j3.0$ $2.7 - j6.9$ $1.7 - j3.4$ $3.8 - j7.5$ $1.7 - j2.9$ <b>n drain efficiency load</b> $1.9 - j6.1$ $2.8 - j2.3$ $2.7 - j6.9$ $2.2 - j1.9$	( $\Omega$ )( $\Omega$ )(W)n power load $1.9 - j6.1$ $1.6 - j3.0$ $375$ $2.7 - j6.9$ $1.7 - j3.4$ $370$ $3.8 - j7.5$ $1.7 - j2.9$ $370$ n drain efficiency load $1.9 - j6.1$ $2.8 - j2.3$ $295$ $2.7 - j6.9$ $2.2 - j1.9$ $280$	$(\Omega)$ $(\Omega)$ $(W)$ $(\%)$ n power load $1.9 - j6.1$ $1.6 - j3.0$ $375$ $60.0$ $2.7 - j6.9$ $1.7 - j3.4$ $370$ $61.0$ $3.8 - j7.5$ $1.7 - j2.9$ $370$ $59.0$ n drain efficiency load $1.9 - j6.1$ $2.8 - j2.3$ $295$ $67.5$ $2.7 - j6.9$ $2.2 - j1.9$ $280$ $67.0$

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.

[2] At 3 dB gain compression.



## 7.3 Recommended impedances for Doherty design

#### Table 11. Typical impedance of main at 1 : 1 load

Measured load-pull data of main device;  $I_{Dq}$  = 800 mA (main);  $V_{DS}$  = 28 V; pulsed CW ( $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %).

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> <sup>[2]</sup>	ղ <mark>ը [2]</mark>	G <sub>p</sub> [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
1800	1.2 – j4.6	1.7 – j3.2	170	38.0	21.0
1845	1.4 – j5.0	1.7 – j2.8	175	38.0	21.0
1880	1.5 – j5.2	1.6 – j2.8	170	39.5	21.5

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.

[2] At P<sub>L(AV)</sub> = 56 W.

#### Table 12. Typical impedance of main device at 1 : 2.5 load

Measured load-pull data of main device;  $I_{Dq}$  = 800 mA (main);  $V_{DS}$  = 28 V; pulsed CW ( $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %).

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <mark>ρ <sup>[2]</sup></mark>	G <sub>p</sub> [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
1800	1.1 – j4.6	3.7 – j1.3	85	54.5	23.5
1845	1.2 – j5.0	3.4 – j1.0	75	54.5	24.0
1880	1.3 – j5.4	3.2 – j0.5	70	54.5	24.0

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.

[2] At P<sub>L(AV)</sub> = 56 W.

#### Table 13. Typical impedance of peak device at 1 : 1 load

Measured load-pull data of peak device;  $I_{Dq} = 1600 \text{ mA}$  (peak);  $V_{DS} = 28 \text{ V}$ ; pulsed CW ( $t_p = 100 \mu \text{s}$ ;  $\delta = 10 \%$ ).

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> <sup>[2]</sup>	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
1800	1.9 – j5.6	2.6 - j3.4	300	27.5	21.0
1845	2.5 – j6.2	2.6 - j3.0	300	27.0	21.0
1880	3.3 – j6.5	2.5 – j2.7	295	27.5	21.5

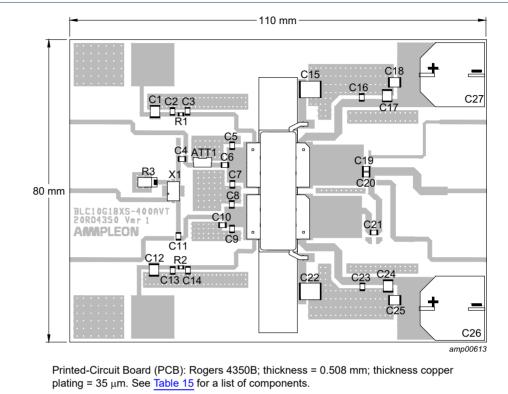
[1]  $Z_{S}$  and  $Z_{L}$  defined in Figure 1.

[2] At P<sub>L(AV)</sub> = 56 W.

#### Table 14. Off-state impedances of peak device

f	Z <sub>off</sub>
(MHz)	(Ω)
1800	1.4 – j2.8
1845	0.9 – j1.7
1880	0.7 – j1.0

**Power LDMOS transistor** 



## 7.4 Test circuit

Fig 2. Component layout

See <u>Figure 2</u> for component layout.				
Component	Description	Value	Remarks	
C1, C12, C17, C18, C24, C25	multilayer ceramic chip capacitor	4μF, 50 V	Murata: GRM32ER71H475KA88L, SMD 1210	
C2, C13	multilayer ceramic chip capacitor	100 nF, 50 V	Murata: SMD 805	
C3, C4, C6, C11, C14, C16, C21, C23	multilayer ceramic chip capacitor	18 pF	Murata: HiQ, SMD 0805	
C5	multilayer ceramic chip capacitor	2.7 pF	Murata: HiQ, SMD 0805	
C7	multilayer ceramic chip capacitor	2.4 pF	Murata: HiQ, SMD 0805	
C8	multilayer ceramic chip capacitor	1.6 pF	Murata: HiQ, SMD 0805	
C9	multilayer ceramic chip capacitor	1.5 pF	Murata: HiQ, SMD 0805	
C10	multilayer ceramic chip capacitor	1.3 pF	Murata: HiQ, SMD 0805	
C15, C22	multilayer ceramic chip capacitor	4.7 μF, 100 V	C5750X7R2A475KT/A	
C19, C20	multilayer ceramic chip capacitor	3.0 pF	Murata: HiQ, SMD 0805	
C26, C27	electrolytic capacitor	470 μF, 63 V	EEVFK1J471M	
R1, R2	resistor	4.7 Ω, 1 %	SMD 805	
R3	resistor	50 Ω, 25 W	Anaren: C16A50Z4	
X1	hybrid coupler	2 dB, 90°	Anaren: Xinger III, X3C20F1-02	
ATT1	attenuator	1 dB	Anaren: D10AA1Z4	

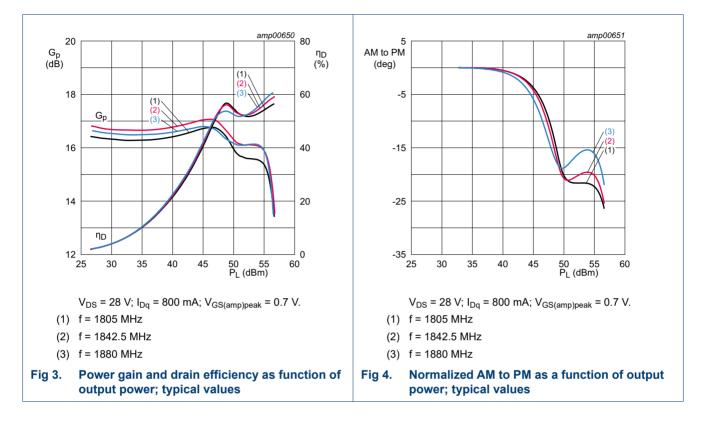
# Table 15. List of components See Figure 2 for component layout

All information provided in this document is subject to legal disclaimers.

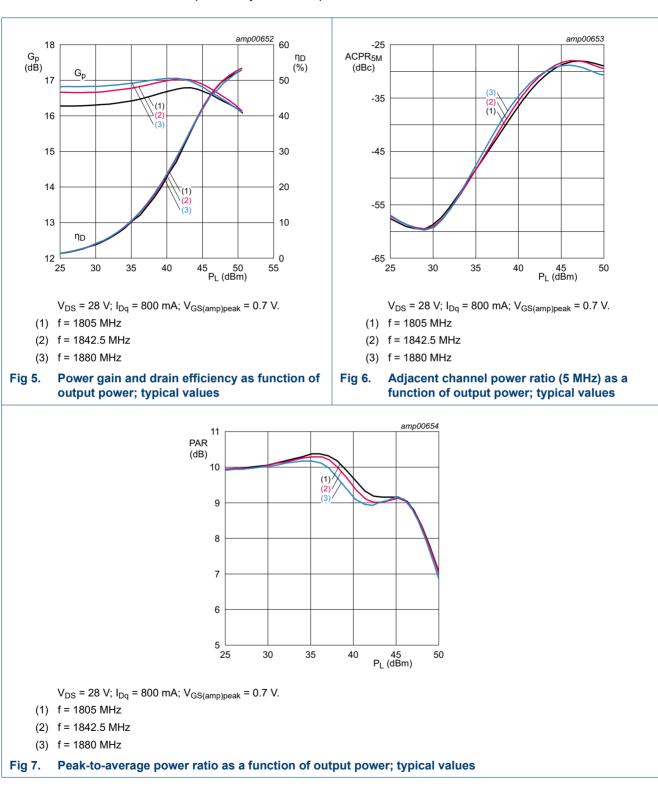
© Ampleon Netherlands B.V. 2018. All rights reserved.

7.5 Graphical data

## 7.5.1 Pulsed CW

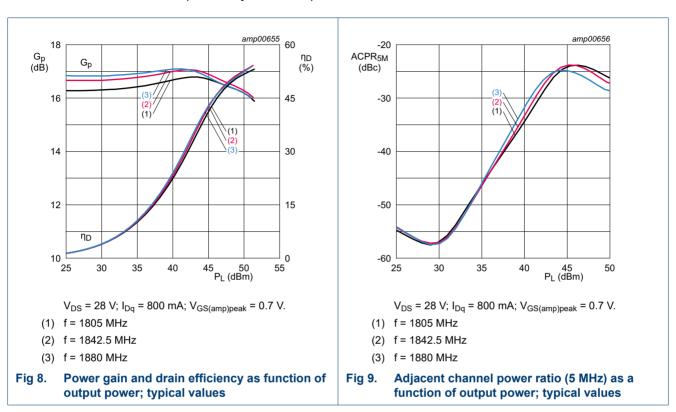


### 7.5.2 1-Carrier W-CDMA



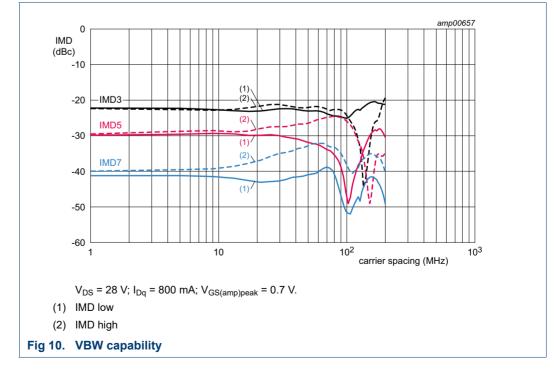
Test signal: 3GPP test model 1; 1 to 64 DPCH (100 % clipping): PAR = 7.5 dB per carrier at 0.01 % probability on CCDF per carrier.

## 7.5.3 2-Carrier W-CDMA



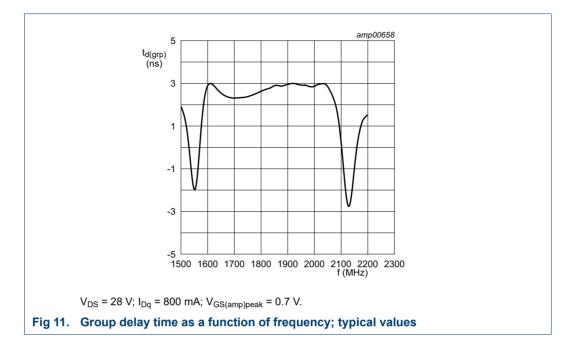
Test signal: 3GPP test model 1; 1 to 64 DPCH (46 % clipping): PAR = 7.5 dB per carrier at 0.01 % probability on CCDF per carrier.

### 7.5.4 2-Tone VBW



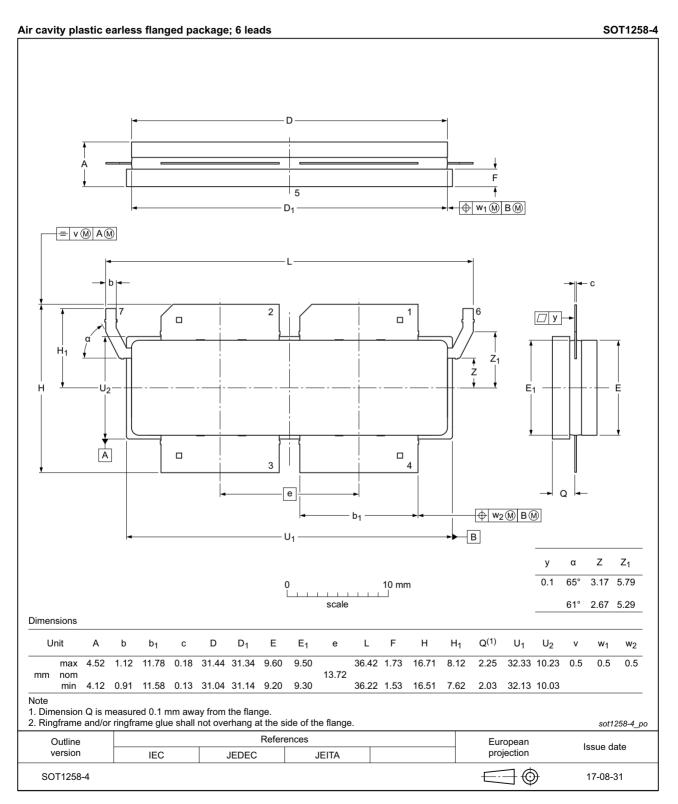
© Ampleon Netherlands B.V. 2018. All rights reserved.

## 7.5.5 Group delay



**Power LDMOS transistor** 

# 8. Package outline



### Fig 12. Package outline SOT1258-4

BLC10G18XS-400AVT

# 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

#### Table 16.ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C3 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

[1] CDM classification C3 is granted to any part that passes after exposure to an ESD pulse of 1000 V.

[2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

# **10. Abbreviations**

#### Table 17.Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
OBO	Output Back Off
PAR	Peak-to-Average Ratio
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

# 11. Revision history

Table 18.         Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC10G18XS-400AVT v.1	20180419	Product data sheet	-	-

# 12. Legal information

## **12.1 Data sheet status**

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

## 12.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Ampleon does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Ampleon sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Ampleon and its customer, unless Ampleon and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Ampleon product is deemed to offer functions and qualities beyond those described in the Product data sheet.

## 12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Ampleon does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Ampleon takes no responsibility for the content in this document if provided by an information source outside of Ampleon.

In no event shall Ampleon be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Ampleon's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Ampleon.

**Right to make changes** — Ampleon reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Ampleon products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an Ampleon product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Ampleon and its suppliers accept no liability for inclusion and/or use of Ampleon products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. Ampleon makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Ampleon products, and Ampleon accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Ampleon product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Ampleon does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Ampleon products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer's third party customer's third party customer's applications and the products or of the application or use by customer's third party customer(s). Ampleon does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Ampleon products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.ampleon.com/terms">http://www.ampleon.com/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Ampleon hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Ampleon products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

BLC10G18XS-400AVT

**Non-automotive qualified products** — Unless this data sheet expressly states that this specific Ampleon product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Ampleon accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Ampleon's warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Ampleon's specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Ampleon for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Ampleon's product specifications.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

## 12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

Any reference or use of any 'NXP' trademark in this document or in or on the surface of Ampleon products does not result in any claim, liability or entitlement vis-à-vis the owner of this trademark. Ampleon is no longer part of the NXP group of companies and any reference to or use of the 'NXP' trademarks will be replaced by reference to or use of Ampleon's own trademarks.

# **13. Contact information**

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

BLC10G18XS-400AVT

# 14. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
2	Pinning information 2
3	Ordering information 2
4	Limiting values 2
5	Thermal characteristics 2
6	Characteristics 3
7	Test information 4
7.1	Ruggedness in Doherty operation
7.2	Impedance information
7.3	Recommended impedances for Doherty design 5
7.4	Test circuit
7.5	Graphical data 8
7.5.1	Pulsed CW
7.5.2	1-Carrier W-CDMA
7.5.3	2-Carrier W-CDMA 10
7.5.4	2-Tone VBW
7.5.5	Group delay 11
8	Package outline 12
9	Handling information
10	Abbreviations 13
11	Revision history 13
12	Legal information 14
12.1	Data sheet status 14
12.2	Definitions 14
12.3	Disclaimers 14
12.4	Trademarks
13	Contact information 15
14	Contents 16

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

#### © Ampleon Netherlands B.V. 2018.

#### B.V. 2018. All rights reserved.

For more information, please visit: http://www.ampleon.com For sales office addresses, please visit: http://www.ampleon.com/sales

Date of release: 19 April 2018 Document identifier: BLC10G18XS-400AVT